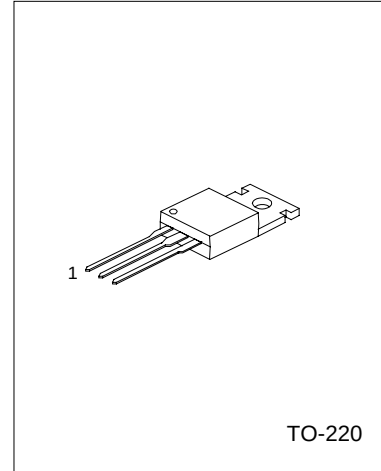


UTC MJE2955T PNP EPITAXIAL SILICON TRANSISTOR

HIGH VOLTAGE TRANSISTOR

DESCRIPTION

The UTC MJE2955T is designed for general purpose of amplifier and switching applications.



1:BASE 2: COLLECTOR 3: EMITTER

ABSOLUTE MAXIMUM RATINGS (Operating temperature range applies unless otherwise specified)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V_{CB0}	70	V
Collector-emitter voltage	V_{CEO}	60	V
Emitter-base voltage	V_{EBO}	5	V
Total Power Dissipation($T_a=25^{\circ}\text{C}$)	P_c	75	W
Collector current	I_c	10	A
Junction Temperature	T_j	150	$^{\circ}\text{C}$
Storage Temperature	T_{STG}	-55 ~ +150	$^{\circ}\text{C}$
Base Current	I_B	6	A

ELECTRICAL CHARACTERISTICS($T_a=25^{\circ}\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-emitter breakdown voltage	BV_{CEO}	$I_c=200\text{mA}$	60			V
Collector-Base Breakdown Voltage	V_{BC0}	$I_c=10\text{mA}$	70			V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_E=10\text{mA}$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=70\text{V}$			1	mA
	I_{CEO}	$V_{CE}=30\text{V}$			700	μA
	I_{CEX}	$V_{CE}=70\text{V}, V_{EB}(\text{off})=1.5\text{V}$			1	mA
Emitter cut-off current	I_{EBO}	$V_{EB}=5\text{V}$			5	mA
Collector-emitter saturation voltage	$V_{CE}(\text{SAT})_1$	$I_c=4\text{A}, I_B=0.4\text{A}$			1.1	V
	$V_{CE}(\text{SAT})_2$	$I_c=10\text{A}, I_B=3.3\text{A}$			8.0	
Base-emitter on voltage	$V_{BE}(\text{ON})$	$V_{CE}=4\text{V}, I_c=4\text{A}$			1.8	V
DC current gain	h_{FE1}	$I_c=4\text{A}, V_{CE}=4\text{V}$	20		100	
	h_{FE2}	$I_c=10\text{A}, V_{CE}=4\text{V}$	5			
Current gain bandwidth product	f_T	$V_{CE}=10\text{V}, I_c=0.5\text{A}, f=1\text{MHz}$	2			MHZ